

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S97	1177	(257/294,659).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 19:05
S98	1001	(438/48,70).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 19:03
S99	23	S97 and ((magnetic adj random adj access adj memory) MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 19:05
S100	16	S98 and ((magnetic adj random adj access adj memory) MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 19:04
S101	1841	(257/294,421,427,659).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 19:05
S102	171	S101 and ((magnetic adj random adj access adj memory) MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 19:05
S105	2799	stray near magnetic adj field	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 08:21
S106	153	S105 and ((magnetic adj random adj access adj memory) MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/24 08:24
S107	47	(substrate wafer die chip 'ic') near S105	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 08:48
S108	4	S107 and ((magnetic adj random adj access adj memory) MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/24 08:30

S109	5	((("6452253") or ("6559521")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/24 08:31
S110	1	("6559521").URPN.	USPAT	OR	OFF	2005/08/24 08:34
S111	6	("4656499" "5288238" "5352925" "5371404" "5490786" "5939772").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/24 08:41
S112	1	("6452253").URPN.	USPAT	OR	OFF	2005/08/24 08:43
S113	6	("4926546" "4953002" "5275975" "5406117" "5561265" "6097080").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/24 08:43
S114	12	S107 and (substrate wafer die chip 'ic') near5 shield	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:24
S115	2	("6515352").URPN.	USPAT	OR	OFF	2005/08/24 08:52
S116	1	10/612676	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 12:20
S117	2	"20040000415"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 12:52
S118	256509	wafer and surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 12:53
S119	31	S118 and magnet\$7 near3 permeable near3 shield	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/24 13:01
S120	31	S118 and magnet\$7 near3 permeabl\$4 near3 shield	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/24 13:02

S12 1	18	S107 and wafer near3 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/24 13:03
S12 2	18	S107 and wafer near3 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:23
S12 3	21387	high adj permeability	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:24
S12 4	201	S123 and (substrate wafer die chip 'ic') near5 shield	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:24
S12 5	23	S124 and S105	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:42
S12 6	83	S123 near3 "100"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:56
S12 7	12	S123 near3 "100\$1"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 13:57